

Taiwan Semiconductor

N-Channel Power MOSFET

FEATURES

- Latest super-junction technology
- Low gate charge capacitance
- High gate noise immunity
- RoHS compliant
- Halogen-free

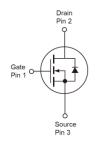
RET PERFURIMANCE PARAMETERS			
PARAMETER	UNIT		
V _{DS} @ T _{j,max}	650	V	
R _{DS(on)} (max)	69	mΩ	
$Q_{g,typ}$	86	nC	

APPLICATIONS

- Switching applications
- HV motor driver
- Industrial







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	600	V
Gate-Source Voltage		V _G s	±30	V
Continuous Drain Current	T _C = 25°C	ID	51	Α
Pulsed Drain Current (Note 1)		Ірм	204	Α
Total Power Dissipation @ T _C = 25°C		P _D	417	W
Single Pulse Avalanche Energy (Note 2)		Eas	780	mJ
Single Pulse Avalanche Current (Note 2)		I _{AS}	5.6	А
Operating Junction and Storage Temperature Range		TJ, TSTG	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	Rелс	0.3	°C/W	
Junction to Ambient Thermal Resistance (Note 3)	Rөja	50	°C/W	

Notes:

- 1. Pulse Width ≤ 100µs.
- 2. L = 50mH, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C.
- 3. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta JA}$ is determined by the user's board design.

1



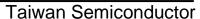
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)	•					
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 1mA$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 3.5 \text{mA}$	V _{GS(TH)}	4	4.8	6	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	Igss			±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 600V, V _{GS} = 0V	I _{DSS}			100	μA
D : 0	V _{GS} = 10V, I _D = 17A	RDS(on)		55	69	mΩ
Drain-Source On-State Resistance	$V_{GS} = 12V, I_D = 17A$			52	60	
Dynamic (Note 5)						
Total Gate Charge		Qg		86		
Gate-Source Charge	$V_{DS} = 480V, I_{D} = 51A,$	Qgs		27		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q _{gd}		50		
Input Capacitance	V _{DS} = 300V, V _{GS} = 0V,	C _{iss}		3566		
Output Capacitance		Coss		99		pF
Reverse Transfer Capacitance	f = 100kHz	Crss		6		
Gate Resistance	f = 1.0Hz	Rg		0.9		Ω
Switching (Note 6)	•					
Turn-On Delay Time		t _{d(on)}		49		
Turn-On Rise Time	$V_{DD} = 300V, R_G = 3.3\Omega,$	t _r		66		
Turn-Off Delay Time	I _D = 51A, V _{GS} = 10V	t _{d(off)}		80		ns
Turn-Off Fall Time		t _f		37		
Source-Drain Diode	·					
Forward Voltage (Note 4)	I _S = 17A, V _{GS} = 0V	V _{SD}		0.9	1.5	V
Reverse Recovery Time	I _S = 25.5A	t _{rr}		465		ns
Reverse Recovery Charge	dI _F /dt = 100A/μs	Qrr		10		μC
	•	•				

Notes:

- 4. Pulse test: Pulse Width $\leq 300 \mu s$, duty cycle $\leq 2\%$.
- Defined by design. Not subject to production test.
- 6. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

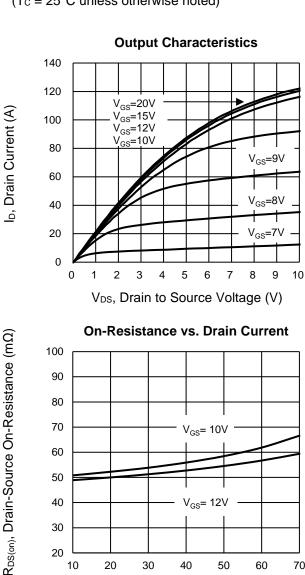
ORDERING CODE	PACKAGE	PACKING
TSM60NE069PW C0G	TO-247	30pcs / Tube

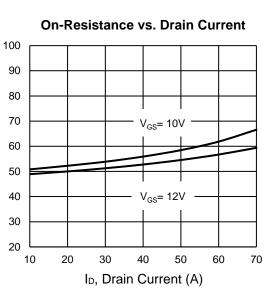


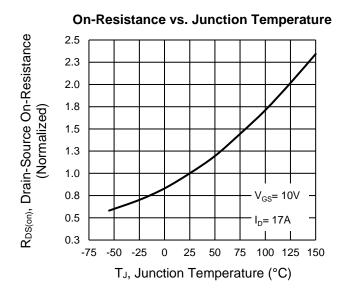


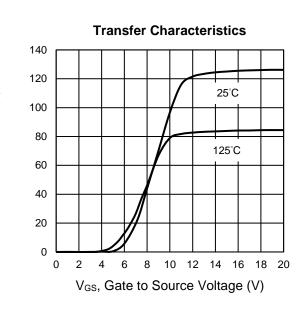
CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)







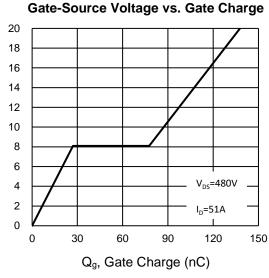


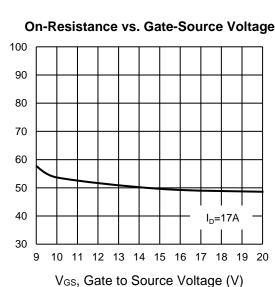
Ip, Drain Current (A)

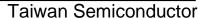
V_{GS}, Gate to Source Voltage (V)

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})},$ Drain-Source On-Resistance (m Ω)

3



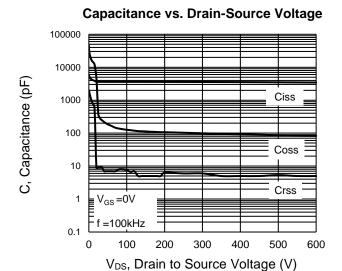


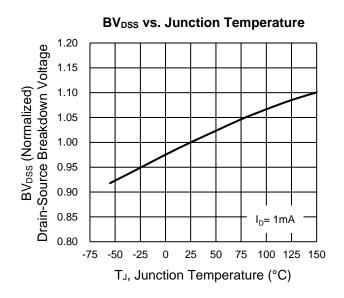




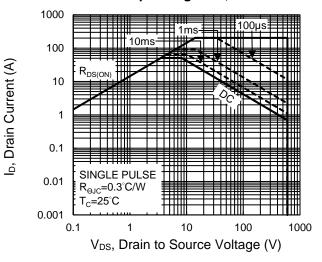
CHARACTERISTICS CURVES

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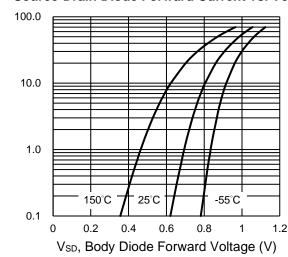
Maximum Safe Operating Area, Junction-to-Case



Normalized Effective Transient

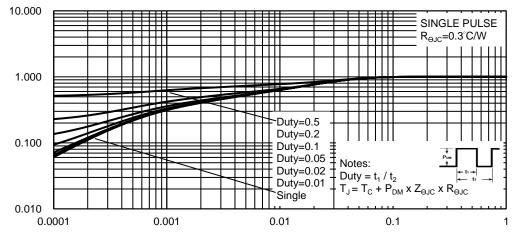
Thermal Impedance, Zeuc

Source-Drain Diode Forward Current vs. Voltage

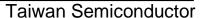


Normalized Thermal Transient Impedance, Junction-to-Case

Reverse Drain Current (A)



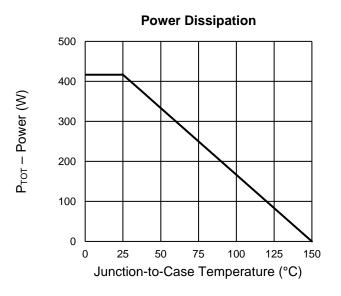
t, Square Wave Pulse Duration (sec)

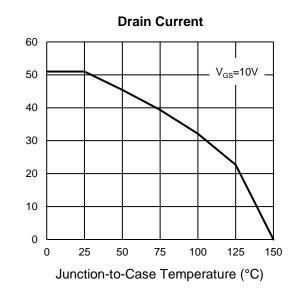




CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

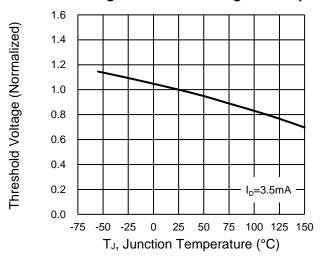




Ip-Drain Current (A)

5

Normalized gate threshold voltage vs Temperature

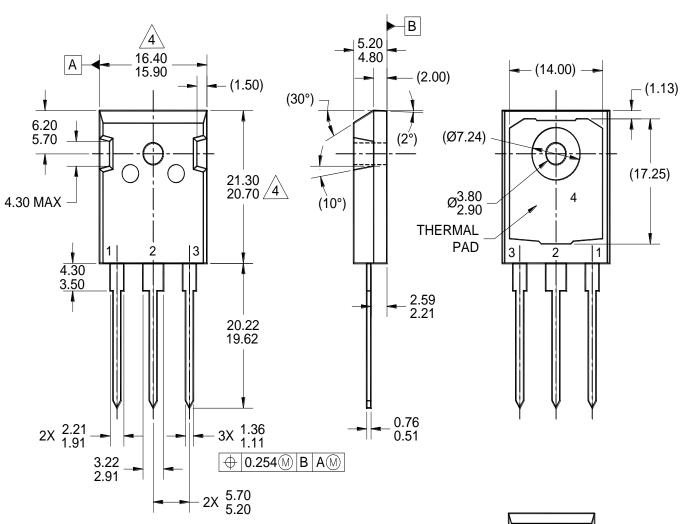




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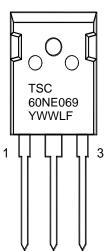
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-247



NOTES: UNLESS OTHERWISE SPECIFIED

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. PACKAGE OUTLINE REFERENCE: JEDEC TO-247, VARIATION AD, ISSUE E.
- MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
- 5. DWG NO. REF: HQ2SD07-TO247AD-071 REV C.



MARKING DIAGRAM

Y = YEAR CODE

WW = WEEK CODE (01~52)

L = LOT CODE (1~9, A~Z)

F = FACTORY CODE



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